

Title (en)  
SEMICONDUCTOR LASER DEVICE

Title (de)  
HALBLEITERLASERVORRICHTUNG

Title (fr)  
DISPOSITIF LASER A SEMI-CONDUCTEUR

Publication  
**EP 1033793 A4 20010418 (EN)**

Application  
**EP 99929803 A 19990713**

Priority

- JP 9903765 W 19990713
- JP 19845798 A 19980714

Abstract (en)  
[origin: EP1033793A1] A semiconductor laser device (100) comprises a first semiconductor laser element (31) and a second semiconductor laser element (32) of different wavelengths, which are mounted on a heat sink block (2) directly or on a sub-mount provided on the heat sink block. The optical axes (A, B) of the semiconductor laser elements are substantially parallel to each other. The first and second semiconductor laser elements (31, 32) are mounted on the heat sink block (2) in such a manner that  $0 \leq L \leq d1 + d2 \leq 160 \mu m$  is satisfied, where d1 is the distance between the optical axis (A) of the first semiconductor laser element (31) and the center axis (O) of a condenser lens (71) arranged in front of the semiconductor laser device (i.e., faced with the emission surfaces of the semiconductor laser elements), d2 is the distance between the optical axis (B) of the second semiconductor laser element (32) and the center axis of the condenser lens, and L is the distance between the optical axes of the first and second semiconductor laser elements. <IMAGE>

IPC 1-7  
**H01S 1/00**; **H01S 5/40**; **G11B 7/125**

IPC 8 full level  
**G11B 7/125** (2006.01); **H01S 5/40** (2006.01); **G11B 7/00** (2006.01); **H01S 5/02** (2006.01)

CPC (source: EP KR US)  
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Citation (search report)

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- See references of WO 0004614A1

Designated contracting state (EPC)  
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